



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



NTUD3171PZ

Small Signal MOSFET

-20 V, -200 mA, Dual P-Channel,
1.0 x 1.0 mm SOT-963 Package



ON Semiconductor®

<http://onsemi.com>

Features

- Dual P-Channel MOSFET
- Offers a Low $R_{DS(on)}$ Solution in the Ultra Small 1.0 x 1.0 mm Package
- 1.5 V Gate Voltage Rating
- Ultra Thin Profile (< 0.5 mm) Allows It to Fit Easily into Extremely Thin Environments such as Portable Electronics.
- This is a Pb-Free Device

Applications

- High Side Switch
- High Speed Interfacing
- Optimized for Power Management in Ultra Portable Equipment

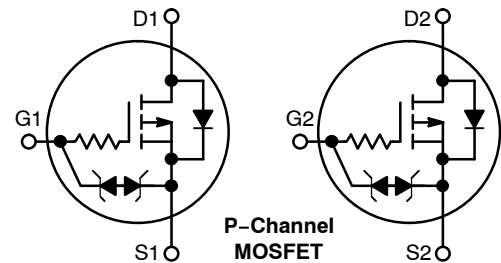
MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter		Symbol	Value	Unit
Drain-to-Source Voltage		V_{DSS}	-20	V
Gate-to-Source Voltage		V_{GS}	± 8	V
Continuous Drain Current (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	-200	mA
			$T_A = 85^\circ\text{C}$	
	$t \leq 5$ s	$T_A = 25^\circ\text{C}$	-250	
Power Dissipation (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	-125	mW
	$t \leq 5$ s		-200	
Pulsed Drain Current		$t_p = 10 \mu\text{s}$	I_{DM}	-600 mA
Operating Junction and Storage Temperature		T_J, T_{STG}	-55 to 150	$^\circ\text{C}$
Source Current (Body Diode) (Note 2)		I_S	-200	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	$^\circ\text{C}$

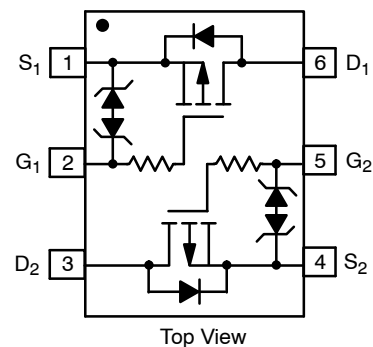
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface-mounted on FR4 board using the minimum recommended pad size, 1 oz Cu.
2. Pulse Test: pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$

$V_{(BR)DSS}$	$R_{DS(ON)}$ MAX	I_D Max
-20 V	5.0 Ω @ -4.5 V	-0.2 A
	6.0 Ω @ -2.5 V	
	7.0 Ω @ -1.8 V	
	10 Ω @ -1.5 V	



PINOUT: SOT-963

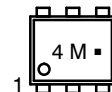


Top View



SOT-963
CASE 527AD

MARKING DIAGRAM



- 4 = Specific Device Code
- M = Date Code
- = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

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THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	1000	°C/W
Junction-to-Ambient – $t = 5$ s (Note 3)		600	

3. Surface-mounted on FR4 board using the minimum recommended pad size, 1 oz Cu.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = -5.0\text{ V}$ $T_J = 25^\circ\text{C}$			-50	nA
		$V_{GS} = 0\text{ V}, V_{DS} = -5.0\text{ V}$ $T_J = 85^\circ\text{C}$			-100	
		$V_{GS} = 0\text{ V}, V_{DS} = -16\text{ V}$ $T_J = 25^\circ\text{C}$			-200	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 5.0\text{ V}$			± 100	nA

ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = -250\ \mu\text{A}$	-0.4		-1.0	V
Drain-to-Source On Resistance	$R_{DS(ON)}$	$V_{GS} = -4.5\text{ V}, I_D = -100\text{ mA}$		2.0	5.0	Ω
		$V_{GS} = -2.5\text{ V}, I_D = -50\text{ mA}$		2.6	6.0	
		$V_{GS} = -1.8\text{ V}, I_D = -20\text{ mA}$		3.4	7.0	
		$V_{GS} = -1.5\text{ V}, I_D = -10\text{ mA}$		4.0	10	
		$V_{GS} = -1.2\text{ V}, I_D = -1.0\text{ mA}$		6.0		
Forward Transconductance	g_{FS}	$V_{DS} = -5.0\text{ V}, I_D = -125\text{ mA}$		0.35		S
Source-Drain Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = -10\text{ mA}$		-0.6	-1.0	V

CHARGES, CAPACITANCES AND GATE RESISTANCE

Input Capacitance	C_{ISS}	$f = 1\text{ MHz}, V_{GS} = 0\text{ V}$ $V_{DS} = -15\text{ V}$		13.5		pF
Output Capacitance	C_{OSS}			3.8		
Reverse Transfer Capacitance	C_{RSS}			2.0		

SWITCHING CHARACTERISTICS, $V_{GS} = 4.5\text{ V}$ (Note 4)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -4.5\text{ V}, V_{DD} = -15\text{ V},$ $I_D = -200\text{ mA}, R_G = 2.0\ \Omega$		26		ns
Rise Time	t_r			46		
Turn-Off Delay Time	$t_{d(OFF)}$			196		
Fall Time	t_f			145		

4. Switching characteristics are independent of operating junction temperatures

ORDERING INFORMATION

Device	Package	Shipping [†]
NTUD3171PZT5G	SOT-963 (Pb-Free)	8000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS

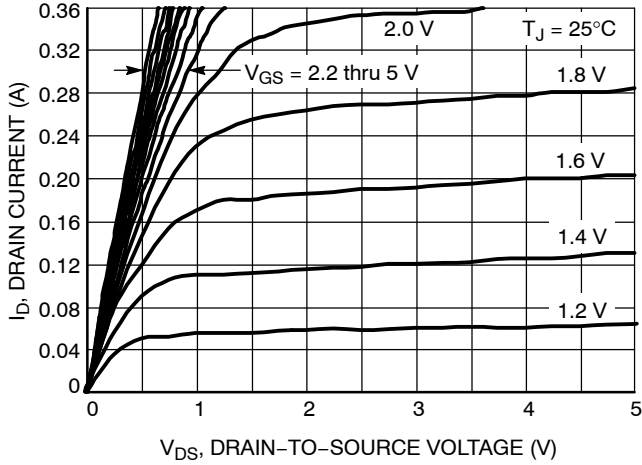


Figure 1. On-Region Characteristics

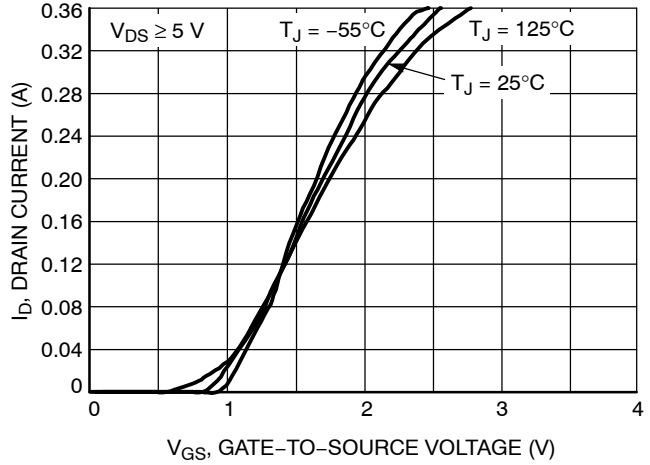


Figure 2. Transfer Characteristics

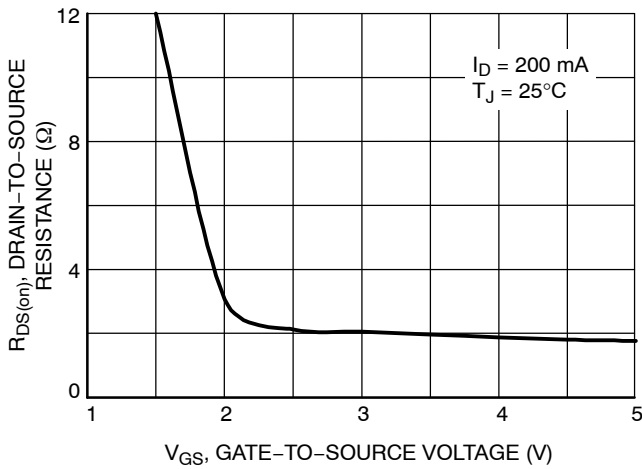


Figure 3. On-Resistance vs. Gate Voltage

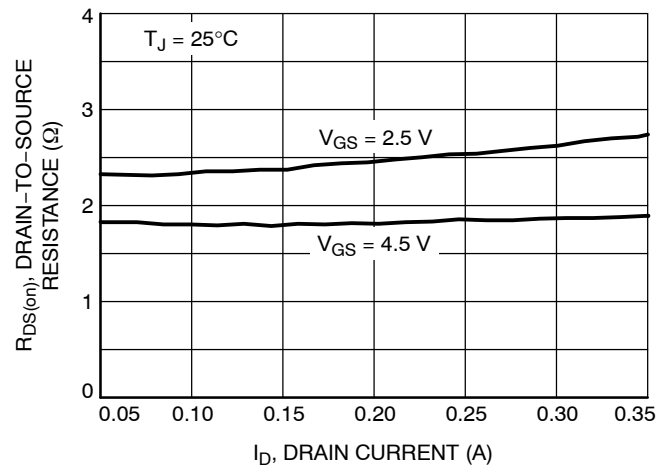


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

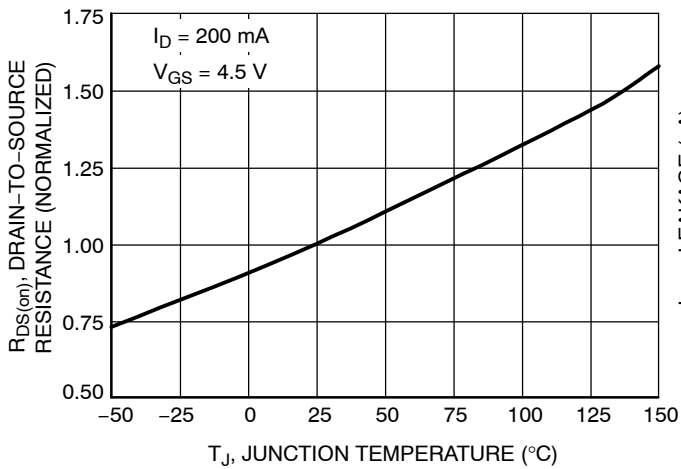


Figure 5. On-Resistance Variation with Temperature

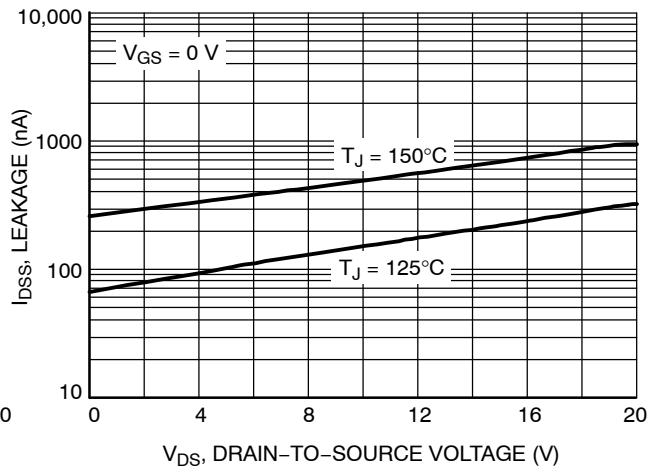


Figure 6. Drain-to-Source Leakage Current vs. Voltage

NTUD3171PZ

TYPICAL CHARACTERISTICS

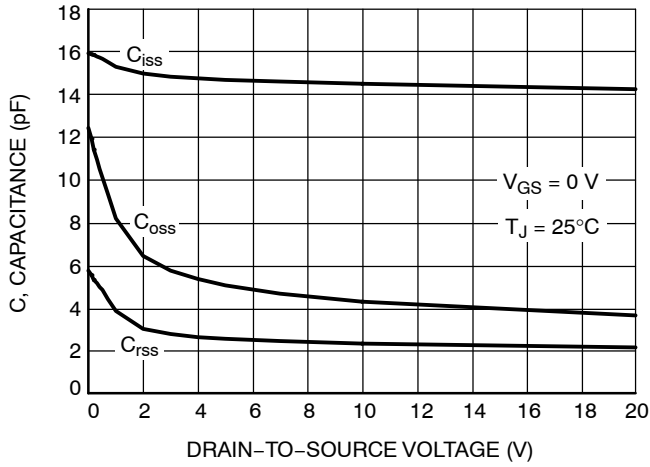


Figure 7. Capacitance Variation

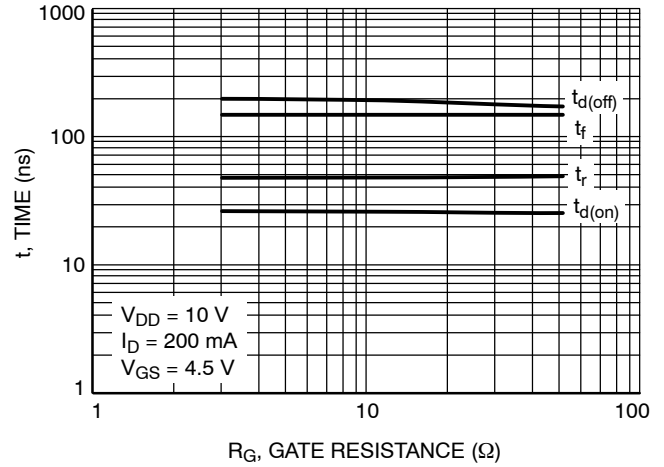


Figure 8. Resistive Switching Time Variation vs. Gate Resistance

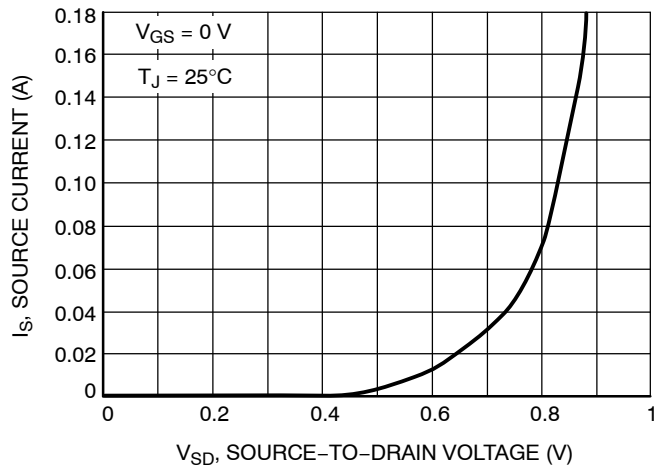
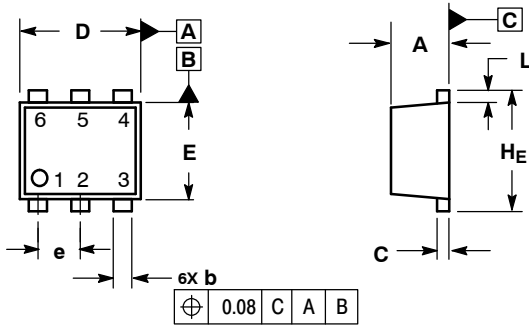


Figure 9. Diode Forward Voltage vs. Current

NTUD3171PZ

PACKAGE DIMENSIONS

SOT-963
CASE 527AD-01
ISSUE D

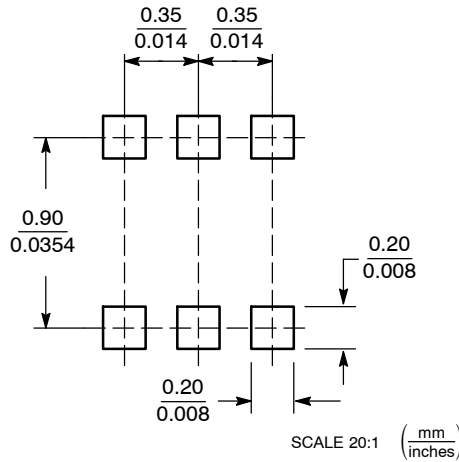


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.34	0.37	0.40			
b	0.10	0.15	0.20	0.004	0.006	0.008
C	0.07	0.12	0.17	0.003	0.005	0.007
D	0.95	1.00	1.05	0.037	0.039	0.041
E	0.75	0.80	0.85	0.03	0.032	0.034
e	0.35 BSC			0.014 BSC		
L	0.05	0.10	0.15	0.002	0.004	0.006
H _E	0.95	1.00	1.05	0.037	0.039	0.041

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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